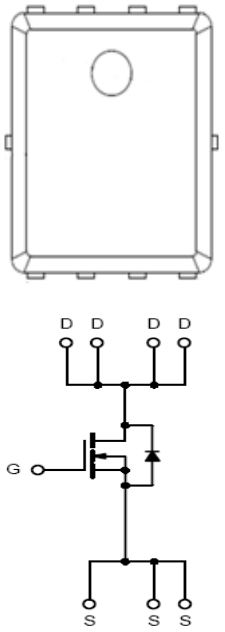
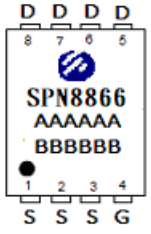
SPN8866
N-Channel Enhancement Mode MOSFET

DESCRIPTION
The SPN8866 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, notebook computer power management and other battery powered circuits where high-side switching is required.

APPLICATIONS
- DC/DC Converter
- Load Switch
- Synchronous Buck Converter

FEATURES
- 80V/80A,$R_{DS(ON)}$=6.0mΩ@V_{GS}=10V
- 80V/80A,$R_{DS(ON)}$=8.5mΩ@V_{GS}=4.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- PPAK5x6-8L package design

PIN CONFIGURATION (PPAK5x6-8L)


PART MARKING


A : Lot Code
B : Date Code
(YY / MM / DD)

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N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN8866DN8RGB	PPAK5x6-8L	SPN8866

※ SPN8866DN8RGB : 13" Tape Reel ; Pb – Free ; Halogen – Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	80	V
Gate –Source Voltage		V_{GSS}	+20/-14	V
Continuous Drain Current(T_J=150℃)	T_C=25℃	I_D	80	A
	T_C=70℃		58	
Pulsed Drain Current		I_{DM}	230	A
Avalanche Current		I_{AS}	58	A
Power Dissipation	T_C=25℃	P_D	83	W
	T_A=70℃		1.6	
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Case		$R_{\theta JC}$	1.5	℃/W

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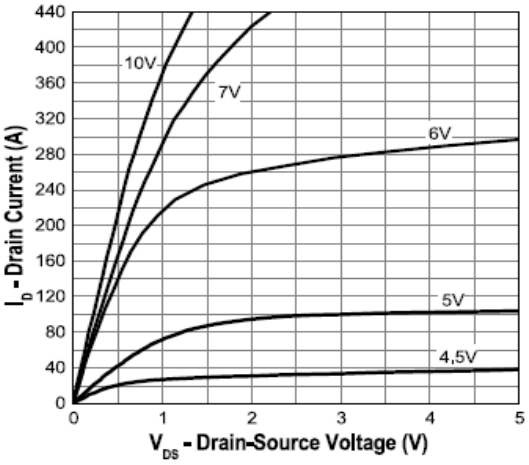
ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

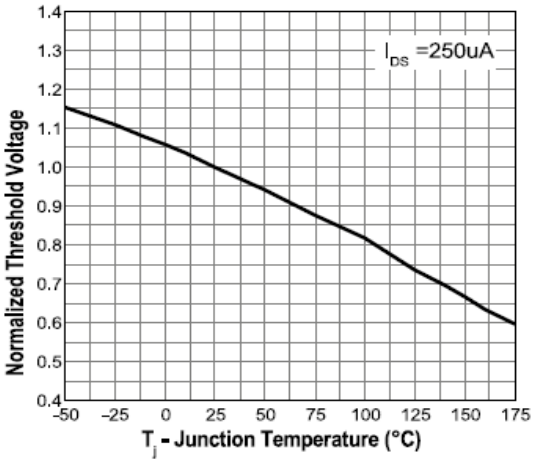
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	80			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.2		2.3	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=+20V/-14V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=64V,V_{GS}=0V			1	uA
		V_{DS}=64V,V_{GS}=0V T_J=85℃			10	
On-State Drain Current	$I_{D(on)}$	V_{DS}≥5V,V_{GS} =10V	80			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=15A			6	mΩ
		V_{GS}=4.5V,I_D=10A			8.5	
Forward Transconductance	gfs	V_{DS}=10V,I_D=5A		10		S
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS} =0V			1	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=64V,V_{GS}=10V I_D=10A		44		nC
Gate-Source Charge	Q_{gs}			7.5		
Gate-Drain Charge	Q_{gd}			12		
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V f=1MHz		2600		pF
Output Capacitance	C_{oss}			350		
Reverse Transfer Capacitance	C_{rss}			20		
Turn-On Time	$t_{d(on)}$	V_{DD}=40V, I_D=1A,V_{GS}=10V R_G=6Ω		10		nS
	t_r			7		
Turn-Off Time	$t_{d(off)}$			36		
	t_f			9		

TYPICAL CHARACTERISTICS

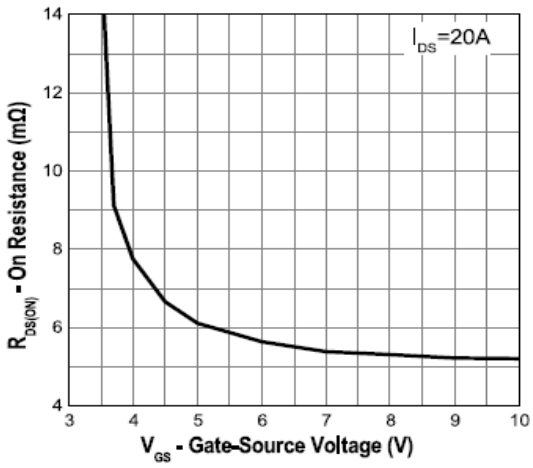
Output Characteristics



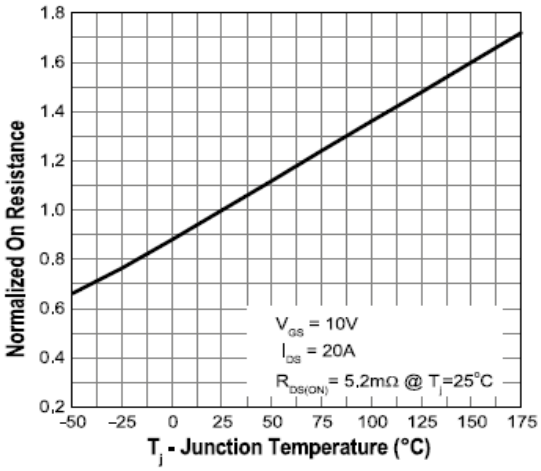
Gate Threshold Voltage



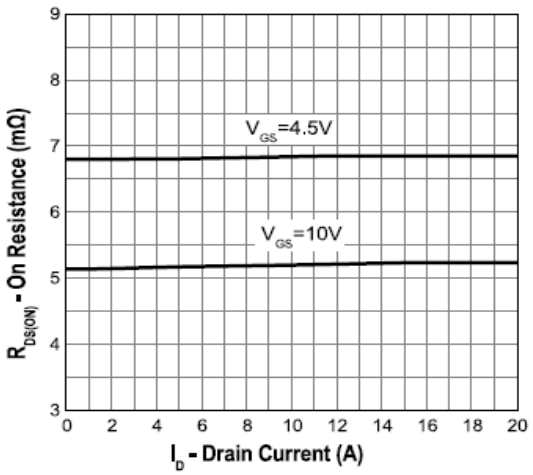
Gate-Source On Resistance



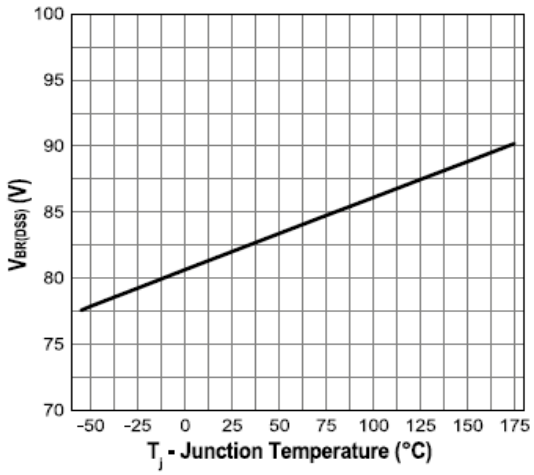
Drain-Source On Resistance



Drain-Source On Resistance

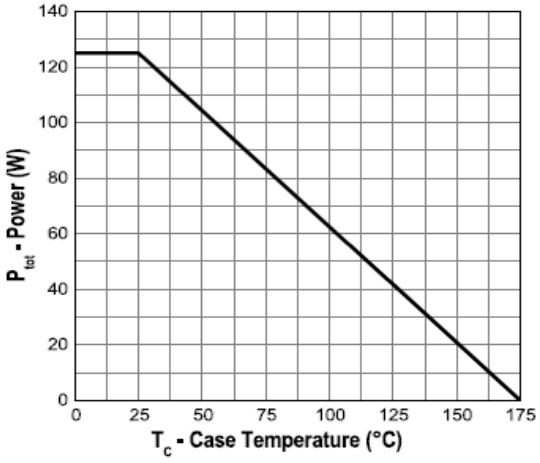


Drain-source Breakdown Voltage

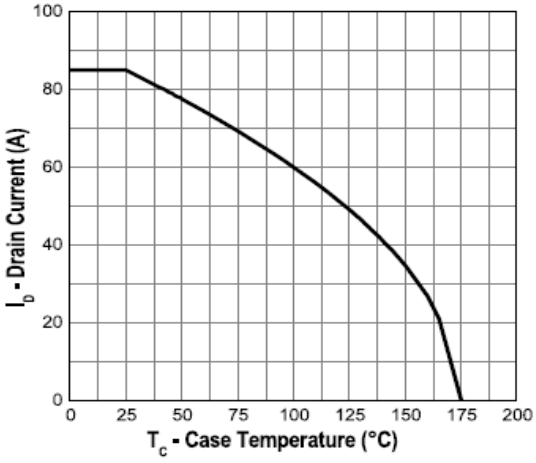


TYPICAL CHARACTERISTICS

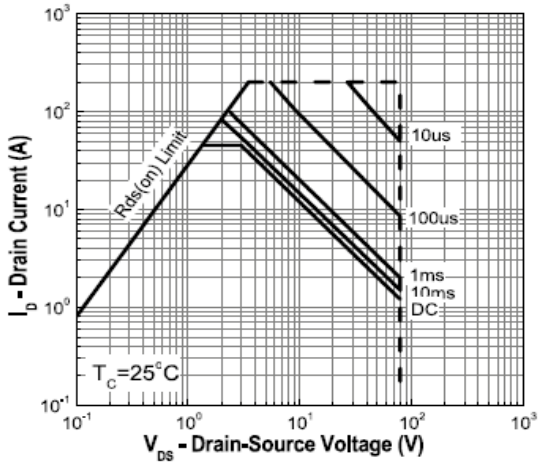
Power Dissipation



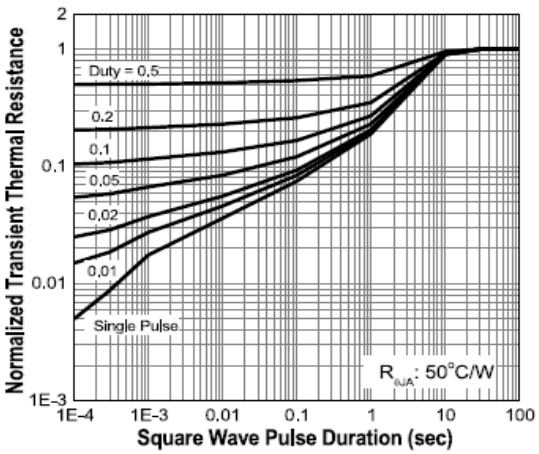
Drain Current



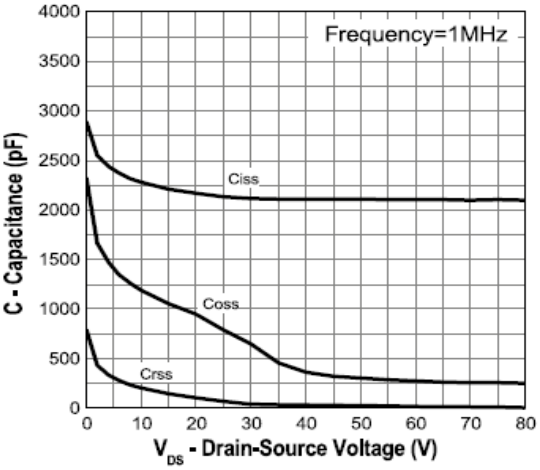
Safe Operation Area



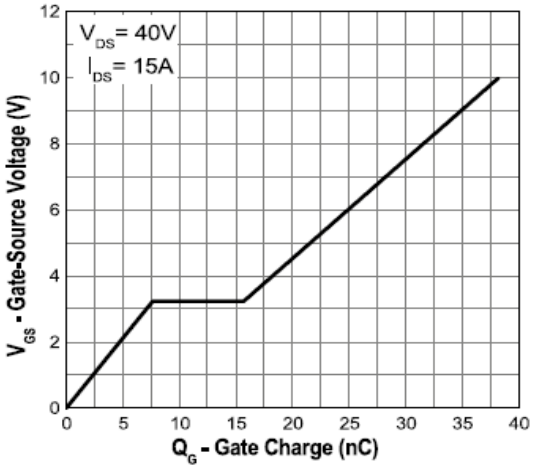
Transient Thermal Impedance



Capacitance



Gate Charge



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